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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yeo, *et al.* Docket No.: TSM03-0553
Serial No.: 10/667,871 Art Unit: 2811
Filed: September 22, 2003 Examiner: TBD
For: Resistor With Reduced Leakage

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Respectfully submitted,

Kristy Engeldahl

Kristy Engeldahl
Legal Assistant

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
Tel: 972-732-1001
Fax: 972-732-9218



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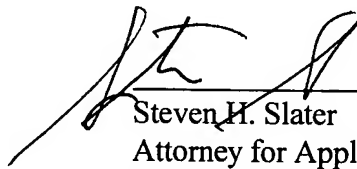
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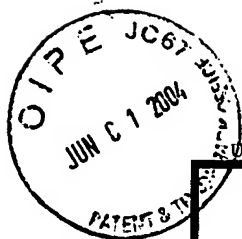
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Respectfully submitted,

May 26, 2004
Date


Steven H. Slater
Attorney for Applicant
Reg. No. 35,361

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
(972) 732-1001 (phone)
(972) 732-9218 (fax)



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				Application Number	10/667,871
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Filing Date	September 22, 2003
				First Named Inventor	Yeo, et al.
				Art Unit	2811
				Examiner Name	TBD
				Attorney Docket Number	TSM03-0553
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
	1	US-4,631,803	12-30-1986	Hunter, et al.	
	2	US-4,946,799	08-07-1990	Blake, et al.	
	3	US-5,447,884	09-05-1995	Fahey, et al.	
	4	US-5,461,250	10-24-1995	Burghartz, et al.	
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	8	US-6,046,487	04-04-2000	Benedict, et al.	
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FOREIGN PATENT DOCUMENTS						
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				Application Number	10/667,871
				Filing Date	September 22, 2003
				First Named Inventor	Yeo, <i>et al.</i>
				Group Art Unit	2811
				Examiner Name	TBD
				Attorney Docket Number	TSM03-0553
Sheet	2	of	3		

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite ¹ No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	23	ISMAIL, K., <i>et al.</i> , "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
	24	NAYAK, D.K., <i>et al.</i> , "Enhancement-Mode Quantum-Well Ge _x Si _{1-x} PMOS," IEEE Electron Device Letters, Vol. 12, No. 4, (April 1991), pp. 154-156.	
	25	GAMIZ, F., <i>et al.</i> , "Strained-Si/SiGe-on-Insulator Inversion Layers: The Role of Strained-Si Layer Thickness on Electron Mobility," Applied Physics Letters, Vol. 80, No. 22, (June 3, 2002), pp. 4160-4162.	
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Examiner Signature		Date Considered	

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Sheet	3	of	3		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
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	36	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.	
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